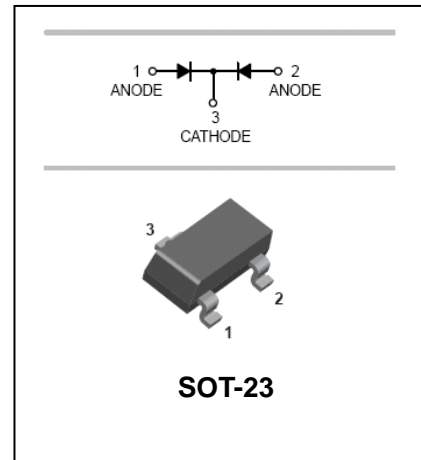


## Low-leakage double diode

## BAV170

### FEATURES

- Plastic SMD package
- Low leakage current: typ. 3pA
- Switching time: typ. 0.8 ms
- Continuous reverse voltage: max. 75V
- Repetitive peak reverse voltage: max. 85V
- Repetitive peak forward current: max. 500mA.



### APPLICATIONS

- Low-leakage current applications in surface mounted circuits.

### ORDERING INFORMATION

Type No.	Marking	Package Code
BAV170	JX	SOT-23

### MAXIMUM RATING @ Ta=25°C unless otherwise specified

Characteristic	Symbol	Limits	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	85	V
DC Reverse Voltage	$V_R$	75	V
Forward Continuous Current	$I_F$	215	mA
single diode loaded double diode loaded		125	
repetitive peak forward current	$I_{FRM}$	500	mA
non-repetitive peak forward current square wave; $T_j=25^\circ\text{C}$ prior to surge;	$I_{FSM}$	4	A
$t_p=1\mu\text{s}$		1	
$t_p=1\text{ms}$ $t_p=1\text{s}$		0.5	
Total Power Dissipation	$P_{tot}$	250	mW
Operating Junction Temperature Range	$T_j$	150	°C
Storage Temperature Range	$T_{STG}$	-65 to +125	°C

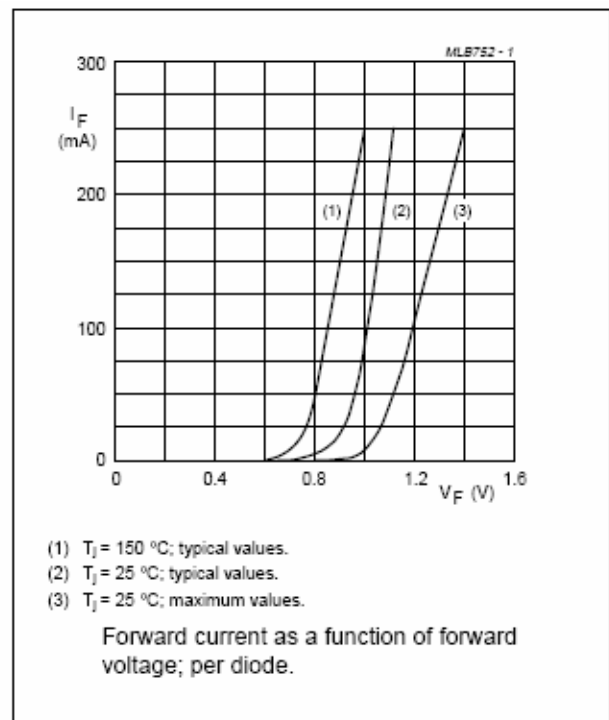
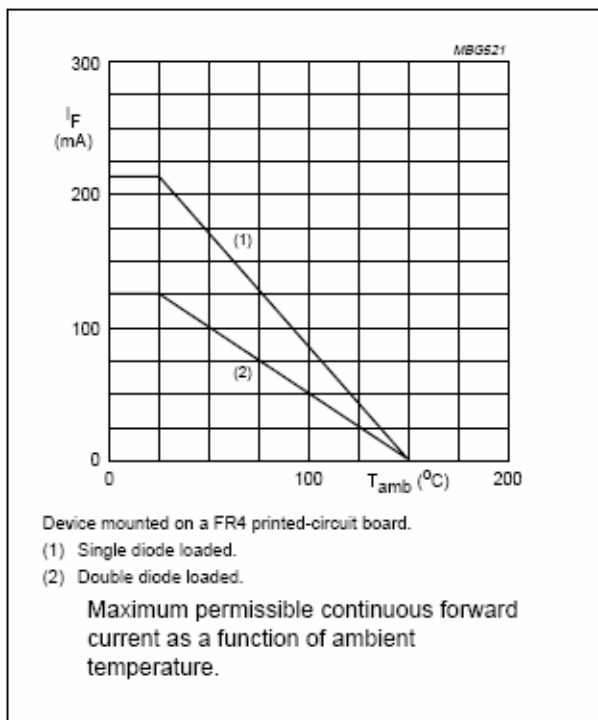
## Low-leakage double diode

## BAV170

### ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

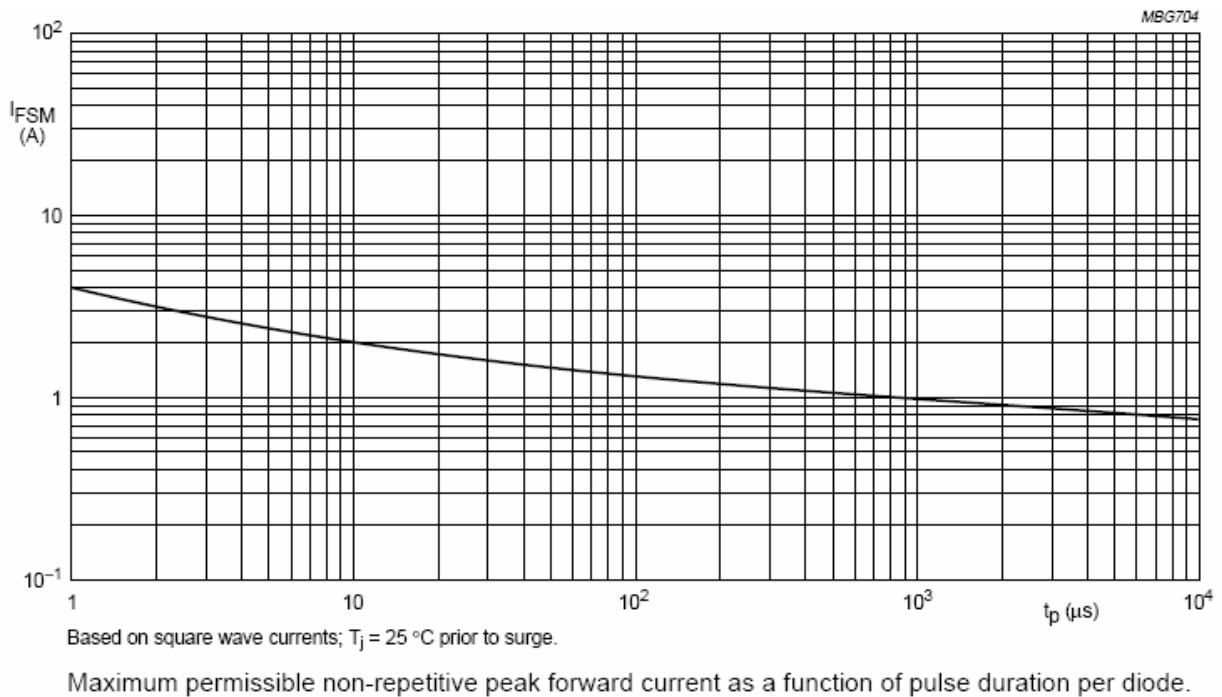
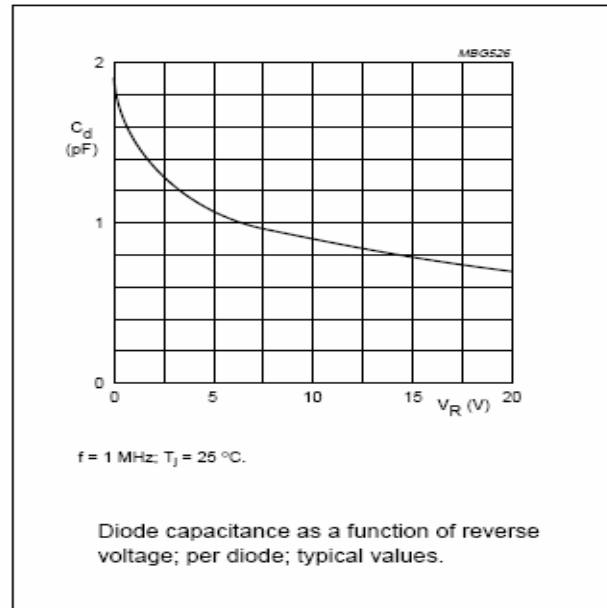
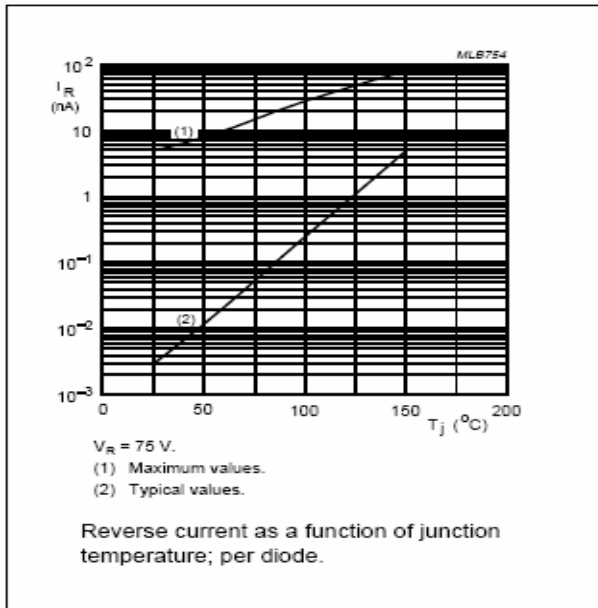
Characteristic	Symbol	Typ	MAX	UNIT	Test Condition
Forward Voltage	$V_F$		900	mV	$I_F=1\text{mA}$
			1000		$I_F=10\text{mA}$
			1100		$I_F=50\text{mA}$
			1250		$I_F=100\text{mA}$
Reverse Leakage Current	$I_R$		5	nA	$V_R=75\text{V}$
Junction Capacitance	$C_j$		2.0	pF	$V_R=0\text{V}, f=1.0\text{MHz}$
Reverse Recovery Time	$t_{rr}$		3	$\mu\text{s}$	$I_F=I_R=10\text{mA}, t_{rr}=0.1 \cdot I_R$

### TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



## Low-leakage double diode

## BAV170



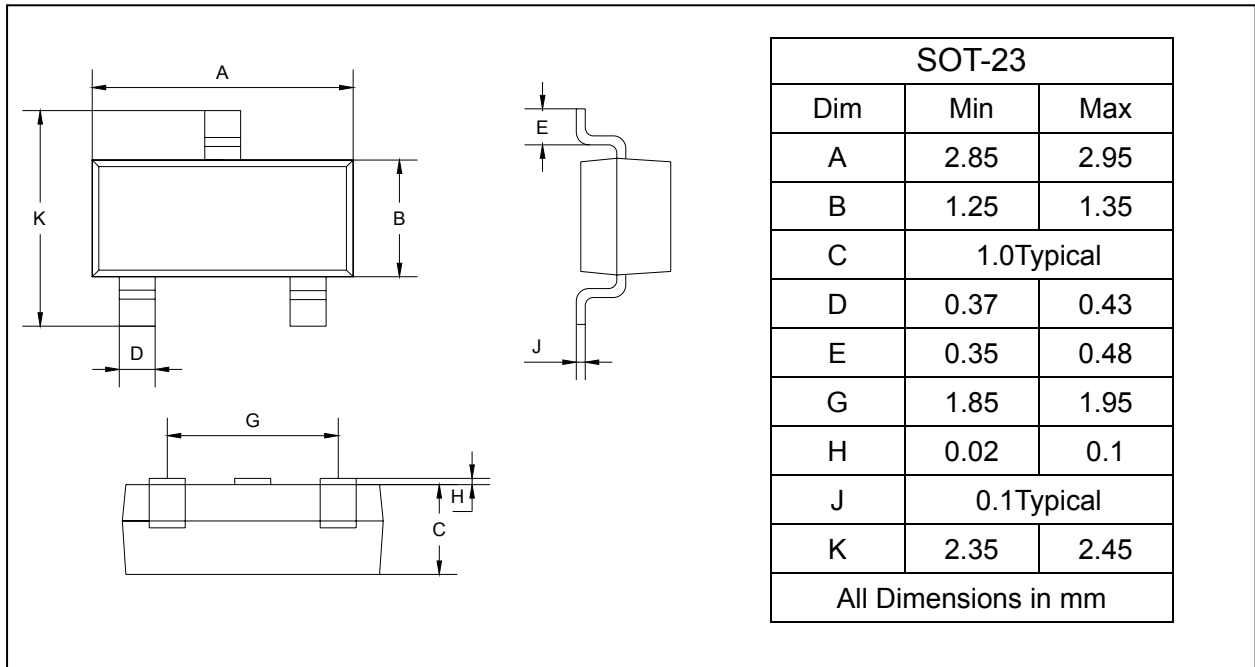
## Low-leakage double diode

## BAV170

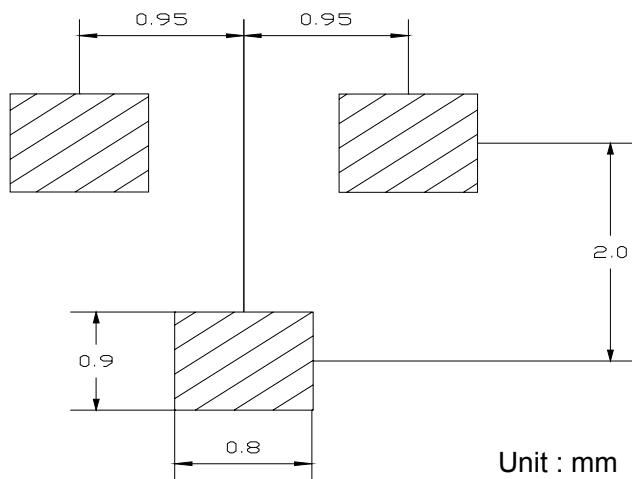
### PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



### SOLDERING FOOTPRINT



### PACKAGE INFORMATION

Device	Package	Shipping
BAV170	SOT-23	3000/Tape&Reel